

MPF201 MPF202 MPF203

CASE 317-01, STYLE 1

DUAL-GATE MOSFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG1} V_{DG2}	30 30	Vdc
Drain Current	I_D	50	mAdc
Gate Current	I_{G1} I_{G2}	± 10 ± 10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.2 8.0	Watt mW/ $^\circ\text{C}$
Lead Temperature	T_L	260	$^\circ\text{C}$
Junction Temperature Range	T_J	-65 to +150	$^\circ\text{C}$
Storage Channel Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($I_D = 10 \mu\text{Adc}$, $V_S = 0$, $V_{G1S} = V_{G2S} = -5.0 \text{ Vdc}$)	$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1-Source Breakdown Voltage(1) ($I_{G1} = \pm 10 \text{ mAdc}$, $V_{G2S} = V_{DS} = 0$)	$V_{(BR)G1SO}$	± 6.0	± 12	± 30	Vdc
Gate 2-Source Breakdown Voltage(1) ($I_{G2} = \pm 10 \text{ mAdc}$, $V_{G1S} = V_{DS} = 0$)	$V_{(BR)G2SO}$	± 6.0	± 12	± 30	Vdc
Gate 1 Leakage Current ($V_{G1S} = \pm 5.0 \text{ Vdc}$, $V_{G2S} = V_{DS} = 0$) ($V_{G1S} = -5.0 \text{ Vdc}$, $V_{G2S} = V_{DS} = 0$, $T_A = 150^\circ\text{C}$)	I_{G1SS}	—	± 0.040	± 100	nAdc μAdc
Gate 2 Leakage Current ($V_{G2S} = \pm 5.0 \text{ Vdc}$, $V_{G1S} = V_{DS} = 0$) ($V_{G2S} = -5.0 \text{ Vdc}$, $V_{G1S} = V_{DS} = 0$, $T_A = 150^\circ\text{C}$)	I_{G2SS}	—	± 0.050	± 100	nAdc μAdc
Gate 1 to Source Cutoff Voltage ($V_{DS} = 15 \text{ Vdc}$, $V_{G2S} = 4.0 \text{ Vdc}$, $I_D = 20 \mu\text{Adc}$)	$V_{G1S}(\text{off})$	-0.5	-1.5	-5.0	Vdc
Gate 2 to Source Cutoff Voltage ($V_{DS} = 15 \text{ Vdc}$, $V_{G1S} = 0$, $I_D = 20 \mu\text{Adc}$)	$V_{G2S}(\text{off})$	-0.2	-1.4	-5.0	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current(2) ($V_{DS} = 15 \text{ Vdc}$, $V_{G1S} = V_{G2S} = 4.0 \text{ Vdc}$)	MPF201, MPF202 MPF203	I_{DSS}	6.0 3.0	13 11	30 15	mAdc
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SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance(3) ($V_{DS} = 15 \text{ Vdc}$, $V_{G2S} = 4.0 \text{ Vdc}$, $V_{G1S} = 0$, $f = 1.0 \text{ kHz}$)	MPF201, MPF202 MPF203	$ Y_{fs} $	8.0 7.0	12.8 12.5	20 15	mmhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{G2S} = 4.0 \text{ Vdc}$, $I_D = I_{DSS}$, $f = 1.0 \text{ MHz}$)		C_{iss}	—	3.3	—	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{G2S} = 4.0 \text{ Vdc}$, $I_D = 10 \text{ mAdc}$, $f = 1.0 \text{ MHz}$)		C_{rss}	0.005	0.014	0.05	pF
Output Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{G2S} = 4.0 \text{ Vdc}$, $I_D = I_{DSS}$, $f = 1.0 \text{ MHz}$)		C_{oss}	—	1.7	—	pF

FUNCTIONAL CHARACTERISTICS

Noise Figure ($V_{DD} = 18 \text{ Vdc}$, $V_{GG} = 7.0 \text{ Vdc}$, $f = 200 \text{ MHz}$) (Figure 1) ($V_{DD} = 18 \text{ Vdc}$, $V_{GG} = 6.0 \text{ Vdc}$, $f = 45 \text{ MHz}$) (Figure 3)	MPF201 MPF203	NF	— —	1.8 5.3	5.0 6.0	dB
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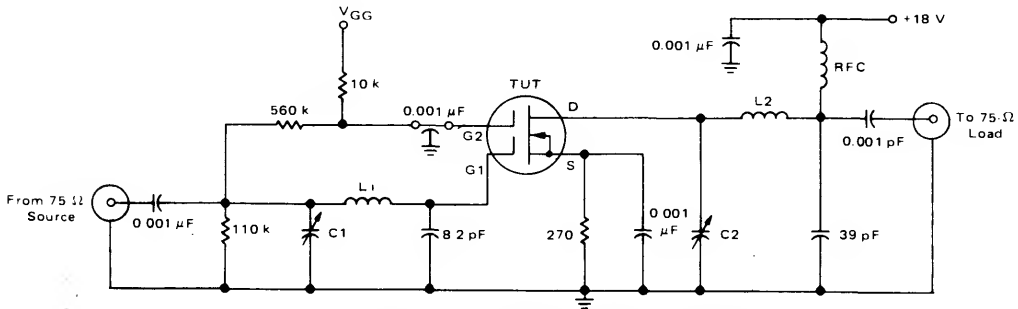
MPF201, MPF202, MPF203

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit	
Common Source Power Gain ($V_{DD} = 18\text{ Vdc}$, $V_{GG} = 7.0\text{ Vdc}$, $f = 200\text{ MHz}$) (Figure 1)	G_{ps}	15	20	25	dB	
($V_{DD} = 18\text{ Vdc}$, $V_{GG} = 6.0\text{ Vdc}$, $f = 45\text{ MHz}$) (Figure 3)	MPF203	20	25	30		
($V_{DD} = 18\text{ Vdc}$, $f_{LO} = 245\text{ MHz}$, $f_{RF} = 200\text{ MHz}$) (Figure 2)	MPF202	15	19	25		
Bandwidth ($V_{DD} = 18\text{ Vdc}$, $V_{GG} = 7.0\text{ Vdc}$, $f = 200\text{ MHz}$) (Figure 1)	BW	5.0	—	9.0	MHz	
($V_{DD} = 18\text{ Vdc}$, $f_{LO} = 245\text{ MHz}$, $f_{RF} = 200\text{ MHz}$) (Figure 2)		4.5	—	7.5		
($V_{DD} = 18\text{ Vdc}$, $V_{GG} = 6.0\text{ Vdc}$, $f = 45\text{ MHz}$) (Figure 3)		3.0	—	6.0		
Gain Control Gate-Supply Voltage(4)	$V_{GG}(GC)$	0	-1.0	-3.0	Vdc	
($V_{DD} = 18\text{ Vdc}$, $\Delta G_{ps} = -30\text{ dB}$, $f = 200\text{ MHz}$) (Figure 1)		MPF201	0	-1.0		-3.0
($V_{DD} = 18\text{ Vdc}$, $\Delta G_{ps} = -30\text{ dB}$, $f = 45\text{ MHz}$) (Figure 3)		MPF203	0	-0.6		-3.0

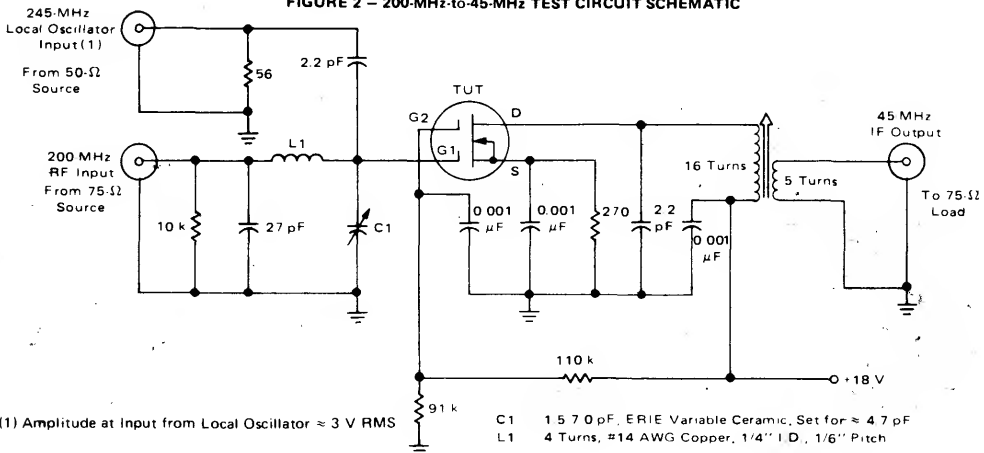
- (1) All gate breakdown voltages are measured while the device is conducting rated gate current. This ensures that the gate-voltage limiting network is functioning properly.
- (2) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.
- (3) This parameter must be measured with bias voltages applied for less than 5 seconds to avoid overheating.
- (4) ΔG_{ps} is defined as the change in G_{ps} from the value at $V_{GG} = 7.0$ volts (MPF201) and $V_{GG} = 6.0$ volts (MPF203).
- (5) Power Gain Conversion

FIGURE 1 — 200-MHz TEST CIRCUIT SCHEMATIC



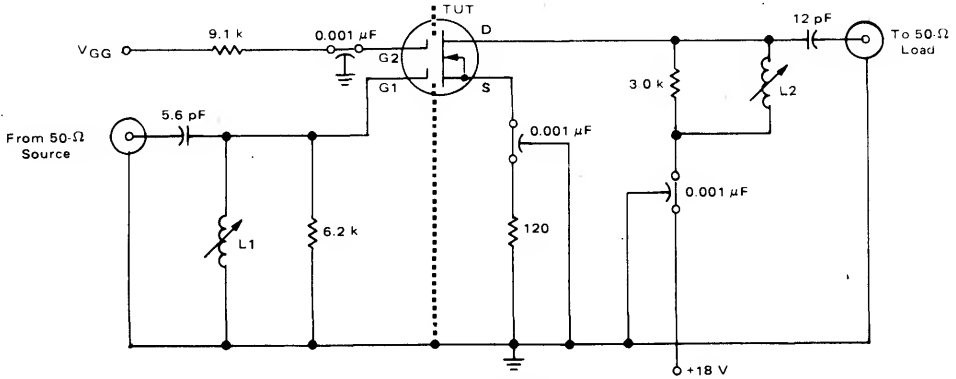
- C1 4.0 ± 0.5 pF, ERIE Variable Ceramic, Set for $\approx 22\text{ pF}$
- C2 4.0 ± 0.30 pF, ERIE Variable Ceramic, Set for $\approx 10\text{ pF}$
- L1 4 Turns, #14 AWG Cooper, 1/4" I.D., 1/6" Pitch
- L2 3 Turns, #14 AWG Cooper, 1/4" I.D., 1/8" Pitch
- RFC DELEVAN No. 153712, 1.0 μH

FIGURE 2 — 200-MHz-to-45-MHz TEST CIRCUIT SCHEMATIC



- (1) Amplitude at Input from Local Oscillator $\approx 3\text{ V RMS}$
- C1 1.5 ± 0.70 pF, ERIE Variable Ceramic, Set for $\approx 4.7\text{ pF}$
- L1 4 Turns, #14 AWG Copper, 1/4" I.D., 1/6" Pitch

FIGURE 3 – 45-MHz TEST CIRCUIT SCHEMATIC



- L1 14 Turns, #30 AWG Copper, Close-Wound 7/32" OD form with ARNOLD ENGINEERING "J" Tuning Core
- L2 10 Turns, #30 AWG Copper, Close-Wound 7/32" OD form with ARNOLD ENGINEERING "J" Tuning Core

TYPICAL CHARACTERISTICS

FIGURE 4 – DRAIN CURRENT versus DRAIN to SOURCE VOLTAGE

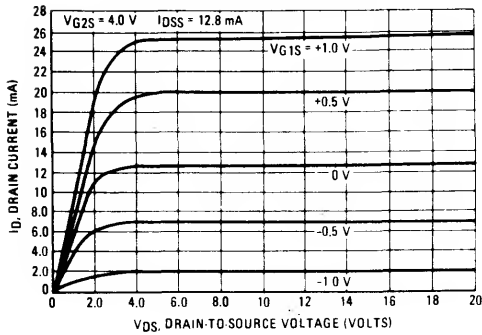


FIGURE 5 – DRAIN CURRENT versus GATE-ONE to SOURCE VOLTAGE

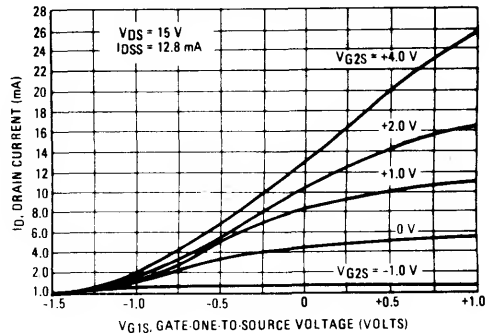


FIGURE 6 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

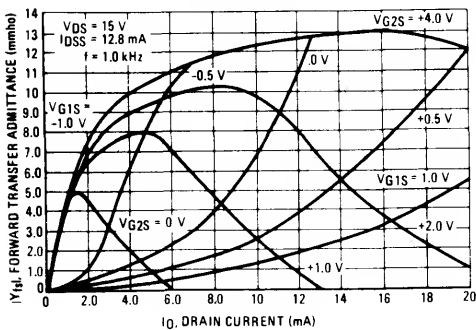
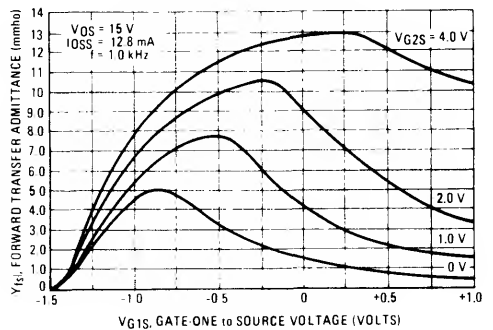


FIGURE 7 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-ONE to SOURCE VOLTAGE



MPF201, MPF202, MPF203

FIGURE 8 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-TWO to SOURCE VOLTAGE

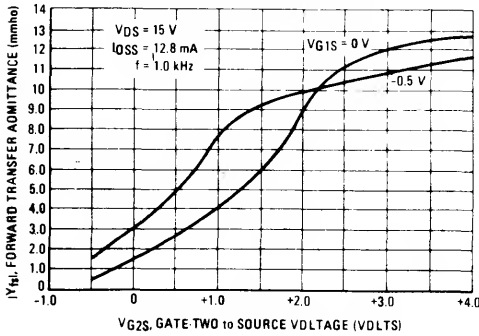


FIGURE 9 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE INPUT AND OUTPUT CAPACITANCE versus GATE-TWO to-SOURCE VOLTAGE

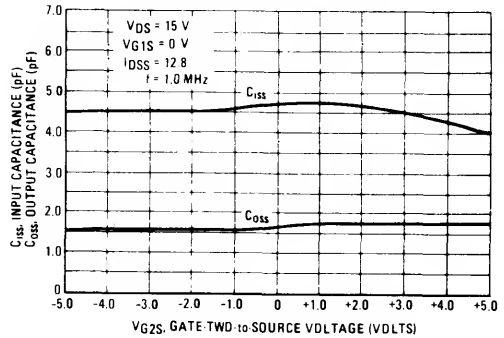


FIGURE 10 – COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus DRAIN CURRENT

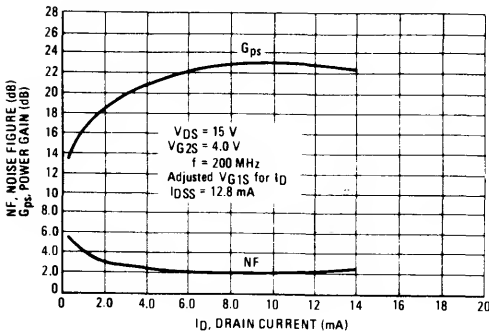
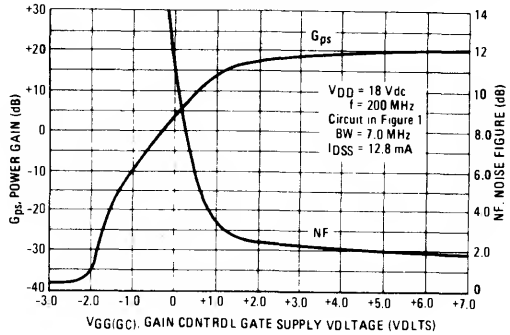


FIGURE 11 – COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus GAIN CONTROL GATE-SUPPLY VOLTAGE – MPF201



6

FIGURE 12 – SMALL-SIGNAL COMMON SOURCE INSERTION POWER GAIN versus GAIN CONTROL GATE-SUPPLY VOLTAGE – MPF203

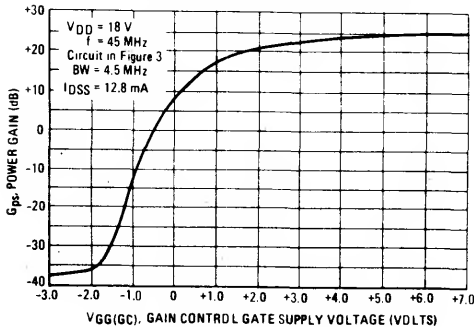
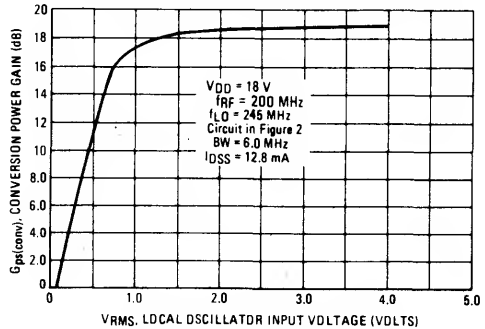


FIGURE 13 – SMALL-SIGNAL COMMON-SOURCE CONVERSION POWER GAIN versus LOCAL OSCILLATOR INPUT VOLTAGE – MPF202



MPF201, MPF202, MPF203

FIGURE 14 — SMALL-SIGNAL GATE ONE FORWARD TRANSFER ADMITTANCE versus FREQUENCY

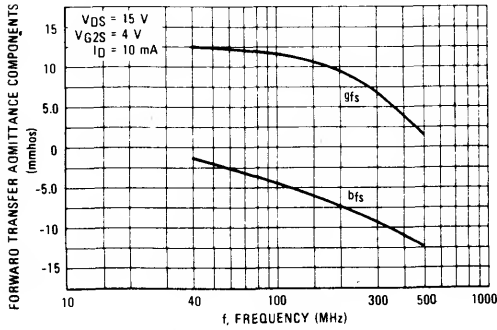


FIGURE 15 — SMALL-SIGNAL GATE ONE INPUT ADMITTANCE versus FREQUENCY

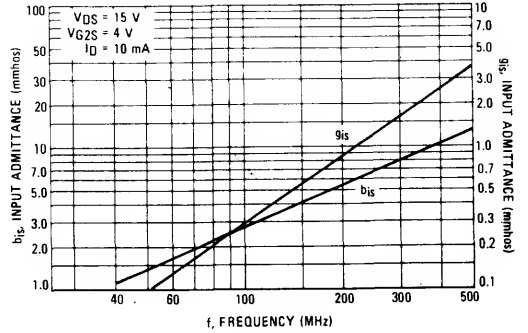


FIGURE 16 — SMALL-SIGNAL GATE ONE OUTPUT ADMITTANCE versus FREQUENCY

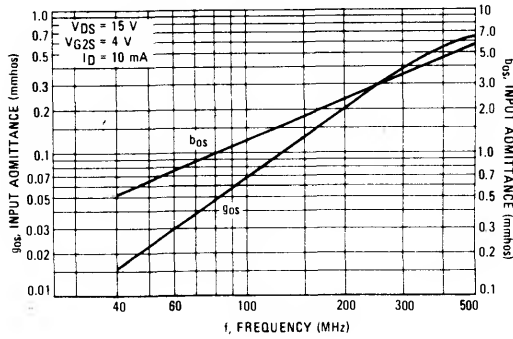


FIGURE 17 — S PARAMETERS PLOTTED ON 50 OHM SMITH CHART

